

FIG.1

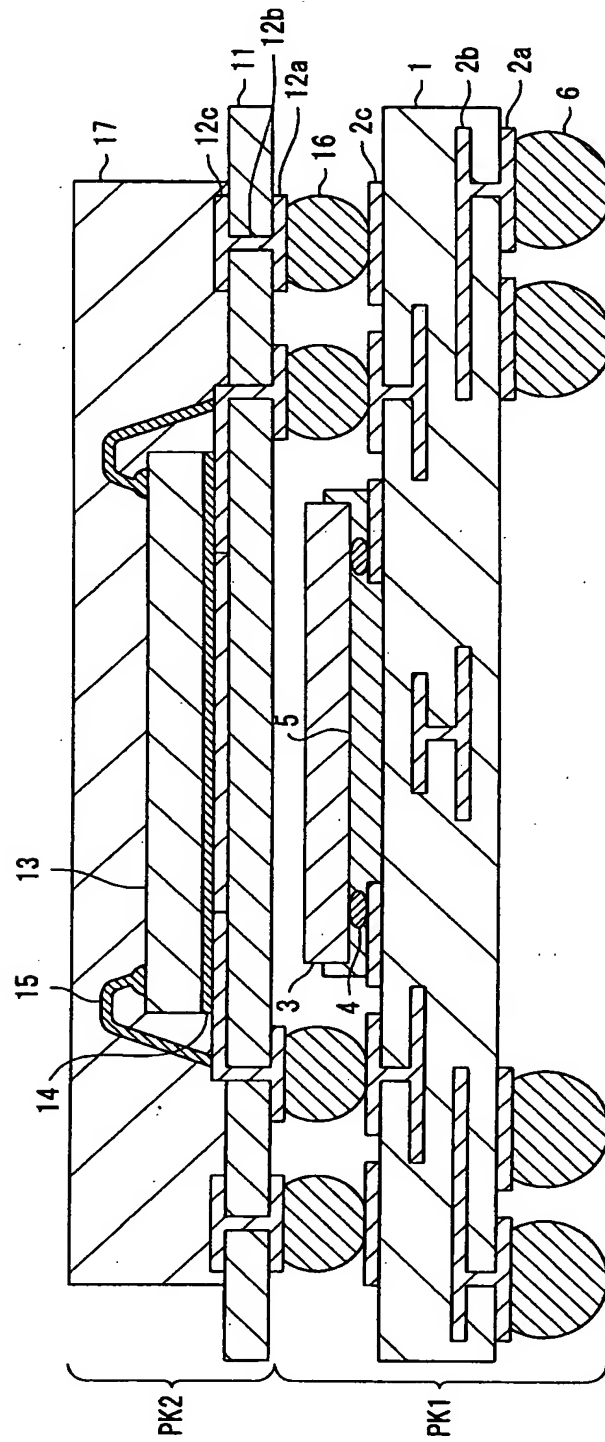


FIG.2

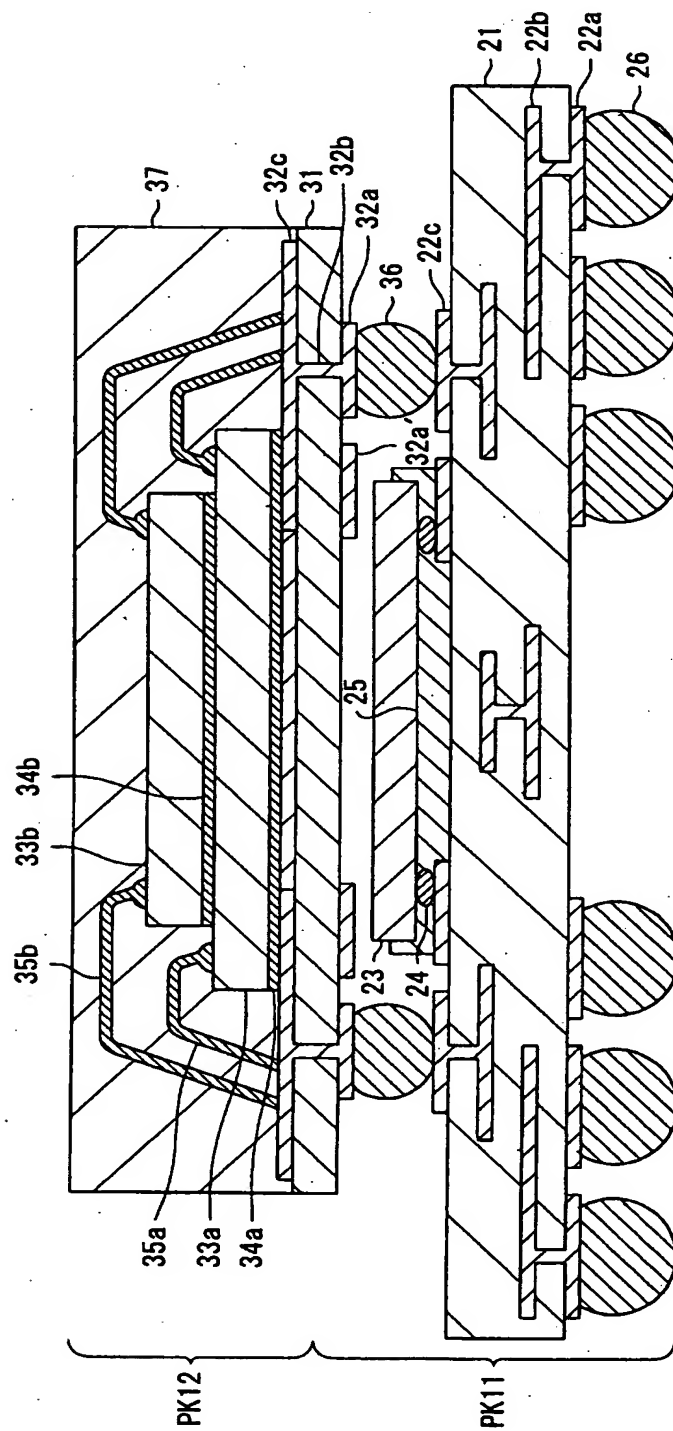


FIG.3

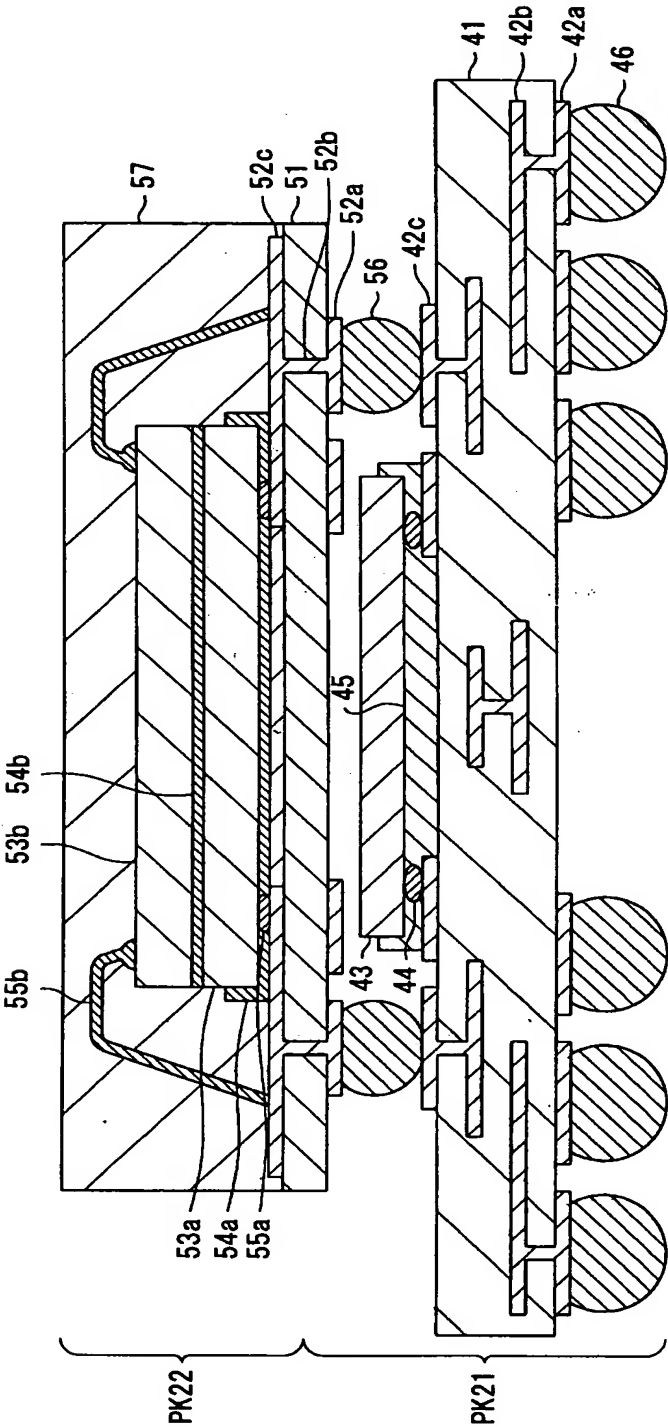


FIG.4A

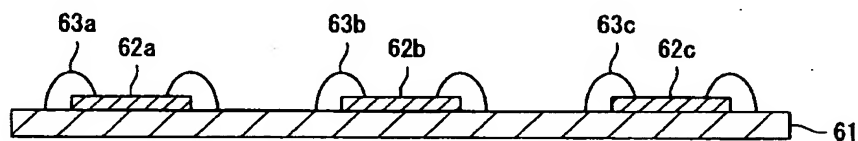


FIG.4B

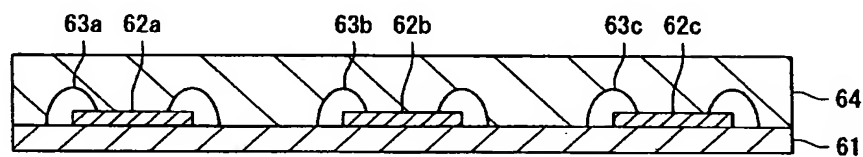


FIG.4C

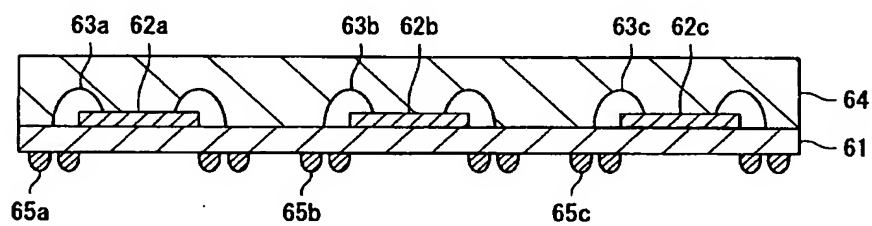


FIG.4D

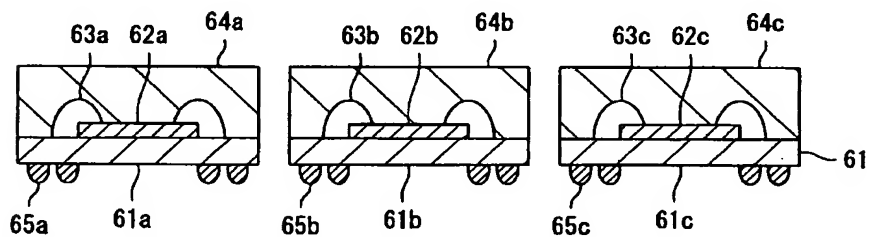


FIG.5A

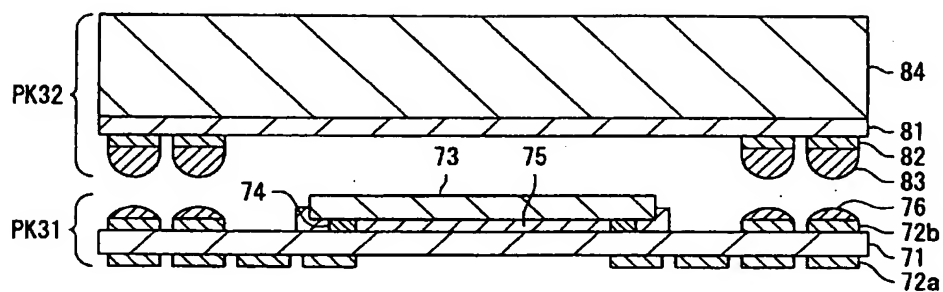


FIG.5B

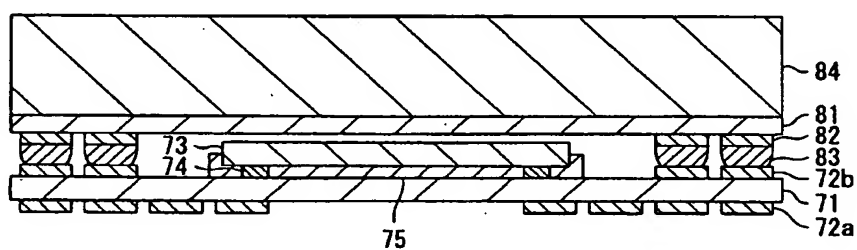
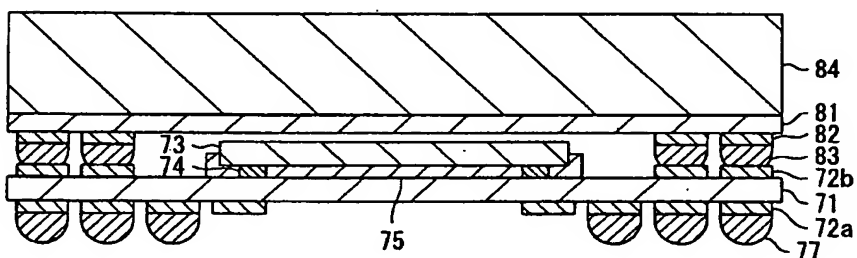


FIG.5C



This cross-sectional diagram illustrates a semiconductor device with a complex layered structure. The main body of the device consists of several horizontal layers: a top layer (101), a middle layer (102) with sub-regions 102a, 102b, and 102c, and a bottom layer (103). A central vertical channel or trench (104) is formed within the device. On the right side, there are four circular components (106) that appear to be solder bumps or contacts, each connected to a horizontal pad (105) on the bottom layer (103). On the left side, there are several vertical structures: a large rectangular block (111) at the top, followed by a thin layer (112), a small rectangular feature (113), a larger rectangular block (114), and a curved, dome-like structure (115) at the bottom left. The layers and components are shown with different hatching patterns to distinguish them.

FIG.7

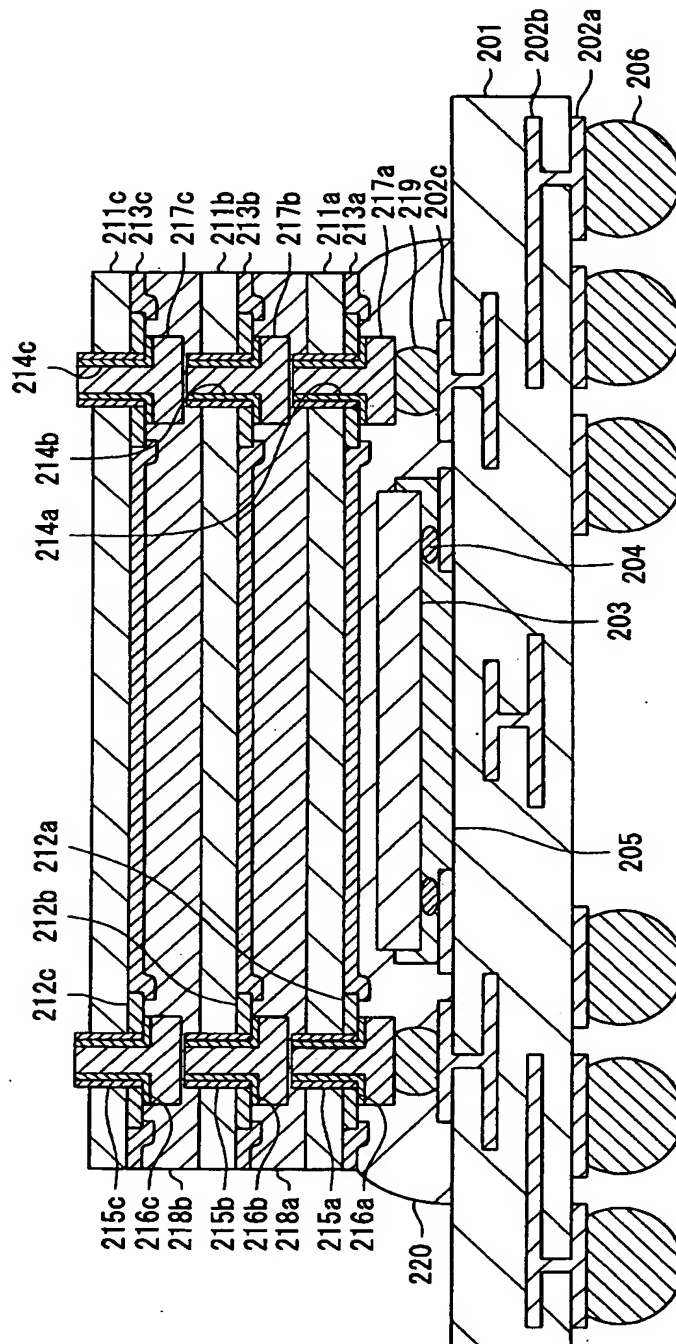


FIG.8

